

# 4V Drive Pch MOSFET

## RRH140P03

### ●Structure

Silicon P-channel MOSFET

### ●Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).

### ●Application

Switching

### ●Packaging specifications

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RRH140P03		○

### ●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V <sub>DSS</sub>	−30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	Continuous	I <sub>D</sub>	±14	A
	Pulsed	I <sub>D</sub> <sup>*1</sup>	±56	A
Source current (Body Diode)	Continuous	I <sub>S</sub>	−1.6	A
	Pulsed	I <sub>sp</sub> <sup>*1</sup>	−56	A
Power dissipation		P <sub>D</sub> <sup>*2</sup>	2.0	W
Channel temperature		T <sub>ch</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	−55 to +150	°C

\*1  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$

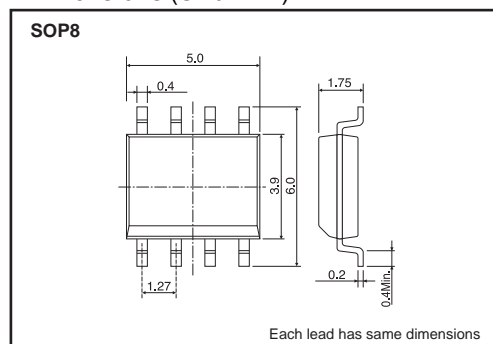
\*2 Mounted on a ceramic board.

### ●Thermal resistance

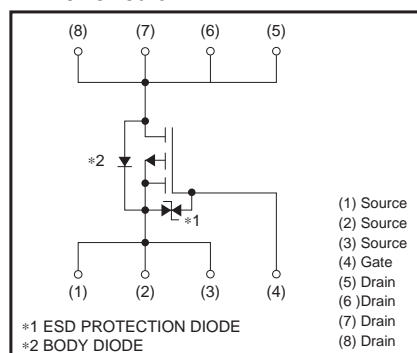
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th(ch-a)}^*$	62.5	°C / W

\* Mounted on a ceramic board.

### ●Dimensions (Unit : mm)



### ●Inner circuit



## ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate-source leakage	I <sub>GSS</sub>	–	–	±10	μA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	–30	–	–	V	I <sub>D</sub> =–1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	–	–	–1	μA	V <sub>DS</sub> =–30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS(th)</sub>	–1.0	–	–2.5	V	V <sub>DS</sub> =–10V, I <sub>D</sub> =–1mA
Static drain-source on-state resistance	R <sub>DS(on)</sub> *	–	5.0	7.0	mΩ	I <sub>D</sub> =–14A, V <sub>GS</sub> =–10V
		–	6.7	9.4		I <sub>D</sub> =–7A, V <sub>GS</sub> =–4.5V
		–	7.3	10.2		I <sub>D</sub> =–7A, V <sub>GS</sub> =–4.0V
Forward transfer admittance	Y <sub>fs</sub>   *	20	–	–	S	I <sub>D</sub> =–14A, V <sub>DS</sub> =–10V
Input capacitance	C <sub>iss</sub>	–	8000	–	pF	V <sub>DS</sub> =–10V
Output capacitance	C <sub>oss</sub>	–	1000	–	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	–	1000	–	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	–	32	–	ns	I <sub>D</sub> =–7A, V <sub>DD</sub> = –15V
Rise time	t <sub>r</sub> *	–	80	–	ns	V <sub>GS</sub> =–10V
Turn-off delay time	t <sub>d(off)</sub> *	–	360	–	ns	R <sub>L</sub> =2.1Ω
Fall time	t <sub>f</sub> *	–	200	–	ns	R <sub>G</sub> =10Ω
Total gate charge	Q <sub>g</sub> *	–	80	–	nC	I <sub>D</sub> =–14A, V <sub>DD</sub> = –15V
Gate-source charge	Q <sub>gs</sub> *	–	18	–	nC	V <sub>GS</sub> =–5V
Gate-drain charge	Q <sub>gd</sub> *	–	30	–	nC	R <sub>L</sub> =1.1Ω
						R <sub>G</sub> =10Ω

\*Pulsed

## ●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	V <sub>SD</sub> *	–	–	–1.2	V	I <sub>S</sub> =–14A, V <sub>GS</sub> =0V

\*Pulsed

## ●Electrical characteristic curves

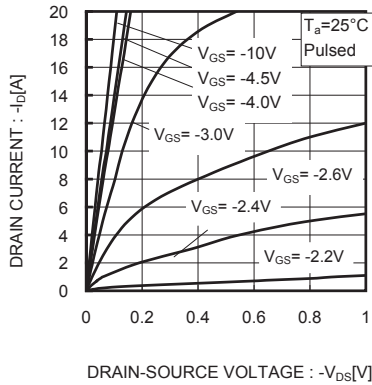


Fig.1 Typical output characteristics( I )

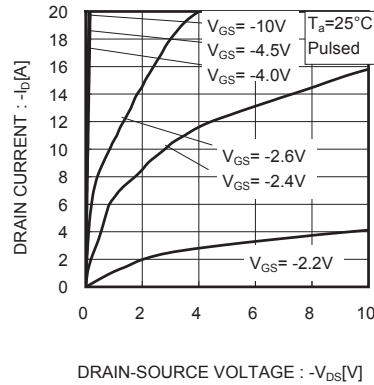


Fig.2 Typical output characteristics( II )

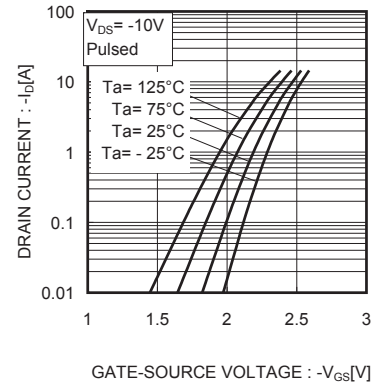


Fig.3 Typical Transfer Characteristics

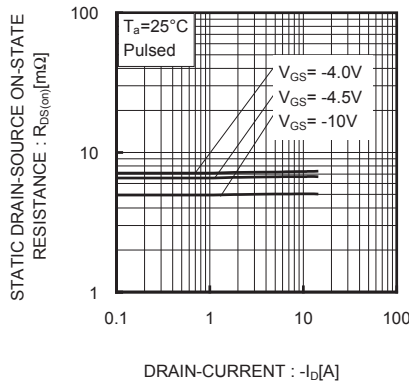


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current( I )

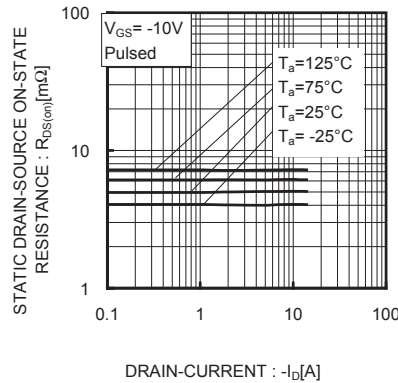


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current( II )

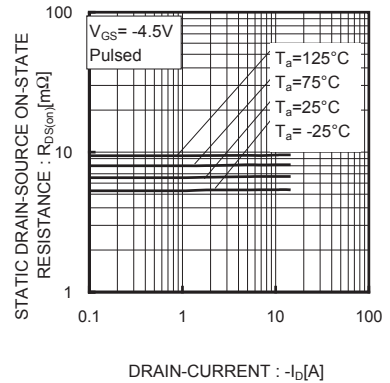


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current( III )

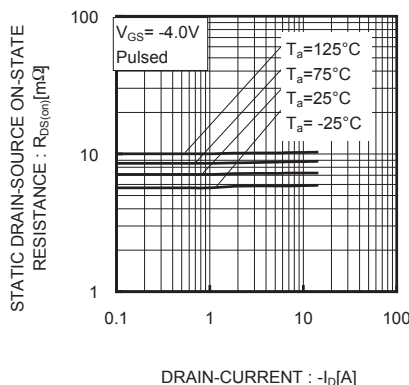


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current( IV )

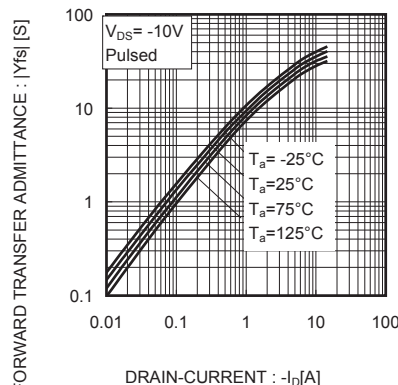


Fig.8 Forward Transfer Admittance vs. Drain Current

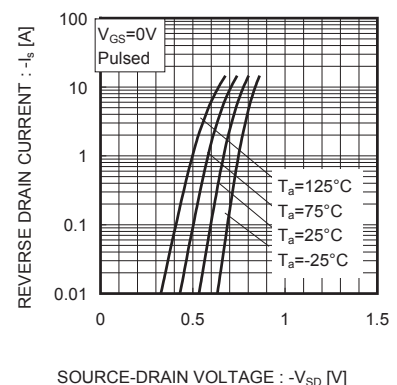


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

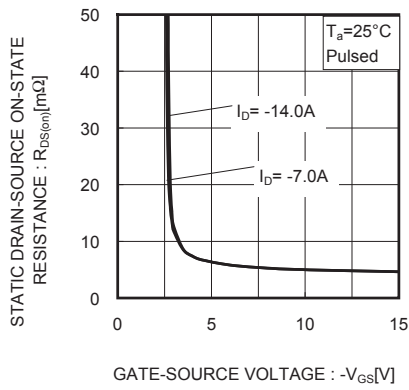


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

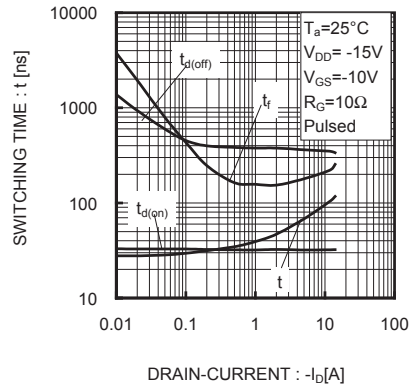


Fig.11 Switching Characteristics

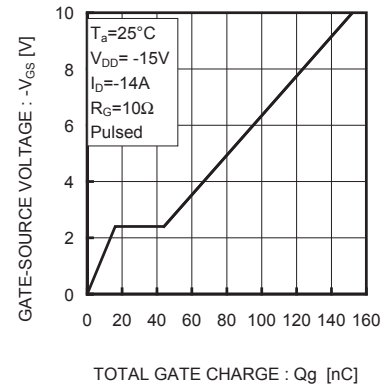


Fig.12 Dynamic Input Characteristics

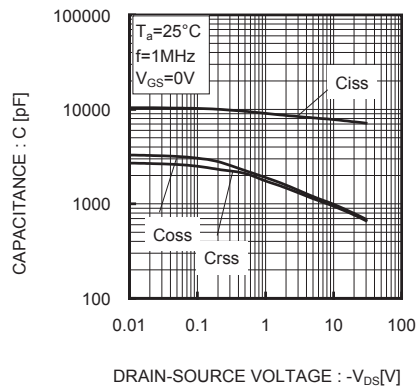


Fig.13 Typical Capacitance vs. Drain-Source Voltage

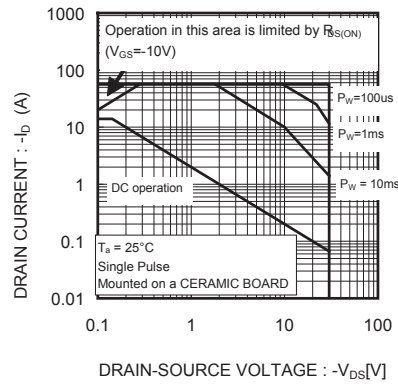


Fig.14 Maximum Safe Operating Area

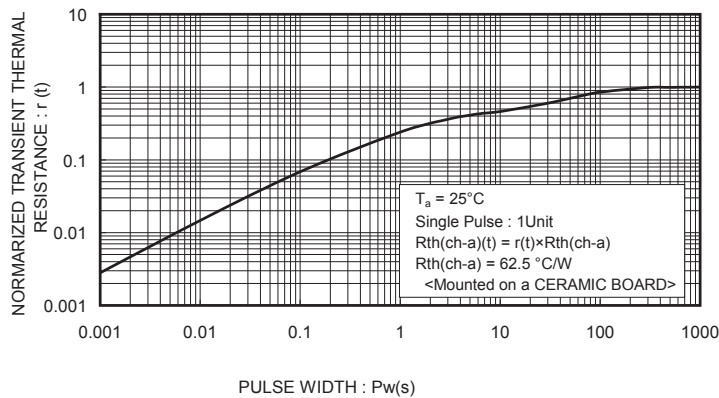


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

●Measurement circuit

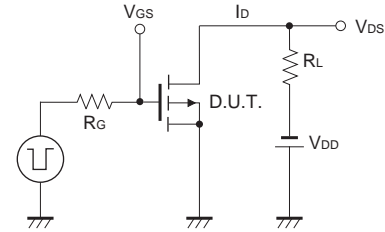


Fig.1-1 Switching Time Measurement Circuit

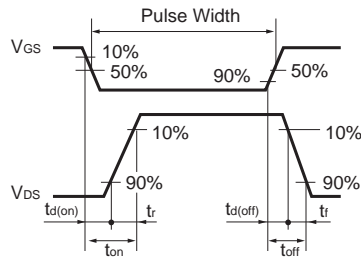


Fig.1-2 Switching Waveforms

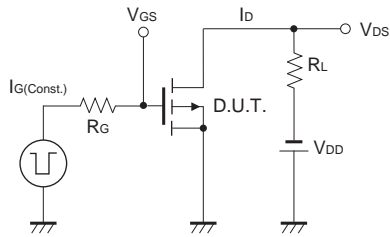


Fig.2-1 Gate Charge Measurement Circuit

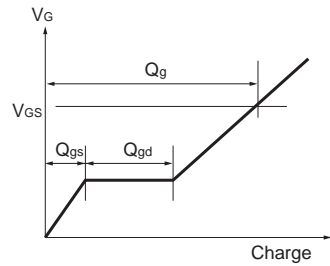


Fig.2-2 Gate Charge Waveform

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